Features

- **1.1 - 3.6 V Operating Voltage Range**
- **4 Non-inverting, Tristatable Drivers for the Following Applications:**
  - **Motor Driver for Bipolar Stepper Motors in Watch/Clock Applications**
  - **Driver for Piezoelectric Transducers (Buzzer)**
  - **LED Driver**
  - **Line Driver for Medium Speed Applications**

Applications

- **Motor Driver**
- **Radio Controlled Clock/Watch**
- **Line Driver for Mini Computer, Laptop**
- **LED Driver**
- **Relay Driver**

Benefits

- **High Load Current at Low Supply Voltage**
- **Replaces Several Discrete Transistors**
- **Tri-state Operation Possible**

Description

The e5130 contains 4 independent driver outputs with an ON resistance of typically 25 Ω (15 Ω) for the P-channel output transistors and typically 20 Ω (13 Ω) for the N-channel output transistors at a supply voltage of 1.5 V (3 V). To obtain a fast transition of the outputs even for slow rise/fall time input signals, all digital inputs (IN1 to IN4) have a Schmitt-trigger characteristic with a hysteresis of typically 50 mV. If a higher driving capability is needed, all inputs and outputs may be connected in parallel. In this case the rise/fall time of the input signals IN1 to IN4 must be less than 200 ns. Due to the fast switching characteristic of the tri-statable output drivers, the circuit is also suited as a low-voltage bus driver.
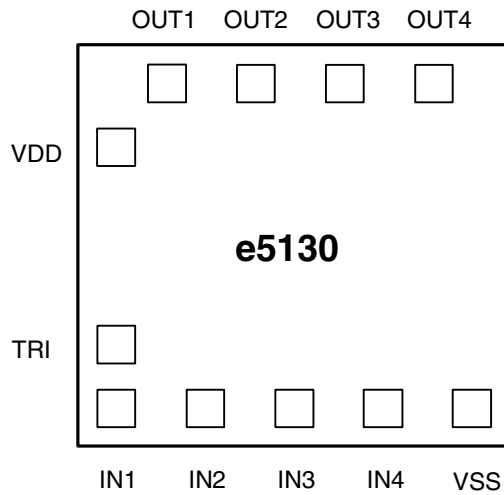
Low Voltage CMOS Driver Circuit

e5130

Pad Configuration

Figure 1. Pinning

Chip size: x = 1.08 mm, y = 1.42 mm,

Pad window: 90 × 90 μ

Pin Description

Symbol	Description
VDD	Positive supply voltage
VSS	Negative supply voltage
IN1 ... IN4	Digital inputs
TRI	Tri-state input
OUT1 ... OUT4	Drive outputs

Absolute Maximum Ratings

Absolute maximum ratings define parameter limits which, if exceeded, may permanently change or damage the device.
All inputs and outputs on circuits are highly protected against electrostatic discharges.
However, precautions to minimize build-up of electrostatic charges during handling are recommended.
The circuits are protected against supply voltage reversal for typically 5 minutes, if the current is limited to 120 mA.

Parameters	Symbol	Value	Unit
Supply voltage	$V_{DD} - V_{SS}$	-0.3 to +5	V
Input voltage range, all inputs	V_I	V_{SS} - 0.3 to V_{DD} + 0.3	V
Operating ambient temperature range		-20 to +70	°C
Storage temperature range		-40 to +125	°C
Lead temperature during soldering at 2 mm distance, 10 s		260	°C

Electrical Characteristics

V_{SS} = 0 V, V_{DD} = +1.5 V, T_{amb} = +25°C, unless otherwise specified. All voltage levels are measured with reference to V_{SS}.

| Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Operating voltage		V_{DD}	1.1		3.6	V
Operating temperature		T_{amb}	-10		60	°C
Operating current (standby)	V_{DD} = 3.6 V, R_{L12} = R_{L34} = R IN1 to IN4 at V_{DD} or V_{SS}, TRI at V_{SS}	I_{DD}		0.05	1	µA
Drive Output OUT1 to OUT4						
Output current	V_{DD} = 1.2 V, R_{L12} = R_{L34} = 200 Ω	I_{OUT}	±4.3	±4.75		mA
Output current	V_{DD} = 1.5 V, R_{L12} = R_{L34} = 200 Ω	I_{OUT}	±5.7	±6.20		mA
Output current	V_{DD} = 3.0 V, R_{L12} = R_{L34} = 200 Ω	I_{OUT}	±12	±13		mA
Delay time	V_{DD} = 3 V, C_L = 50 pF	T_{Dr}, T_{Df}		35	60	ns
Delay time	V_{DD} = 1.5 V, C_L = 50 pF see Figure 3, note 1	T_{Dr}, T_{Df}		80	150	ns
Rise-/fall time	V_{DD} = 3 V, C_L = 50 pF	t_r, t_f		8	15	ns
Rise-/fall time	V_{DD} = 1.5 V, C_L = 50 pF see Figure 3, note 2	t_r, t_f		12	25	ns
Digital Input IN1 to IN4						
Input current	V_{IL} = 0 V	I_{IL}			-100	nA
Input current	V_{IH} = V_{DD}	I_{IH}			100	nA
Threshold	V	V_{TH}		V_{DD}/2		V
Hysteresis	mV	V_{HYST}		50		mV
Tristate Input TRI						
Input current TRI	V_{IH} = V_{DD}	I_{IH}	0.15	0.4	1.2	µA

Figure 2. Test Circuit
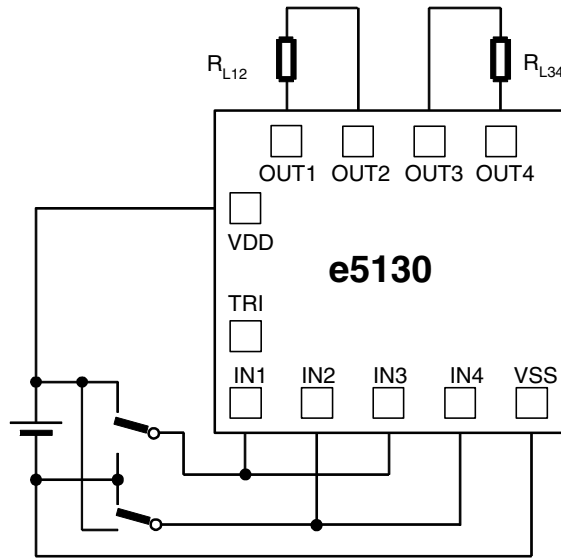
Figure 3. Drive Output Delay Time
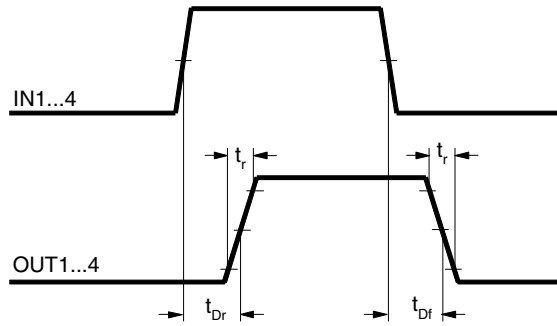
Notes: 1. t_{Dr}, t_{Df} is defined at 50% of supply voltage
2. t_r, t_f is defined from 10% to 90%, resp. 90% to 10% of supply voltage

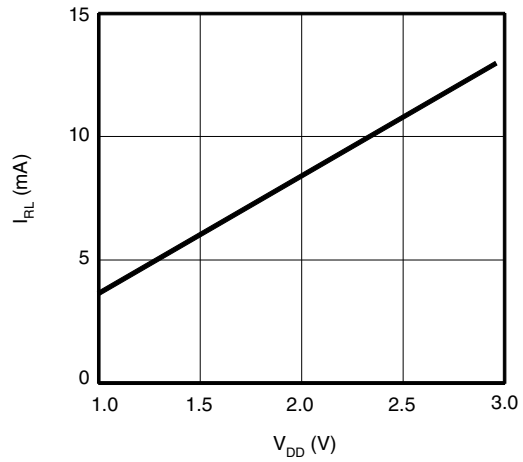**Figure 4.** Typical Current into 200 Ω Load Resistor, Condition as per Figure 2

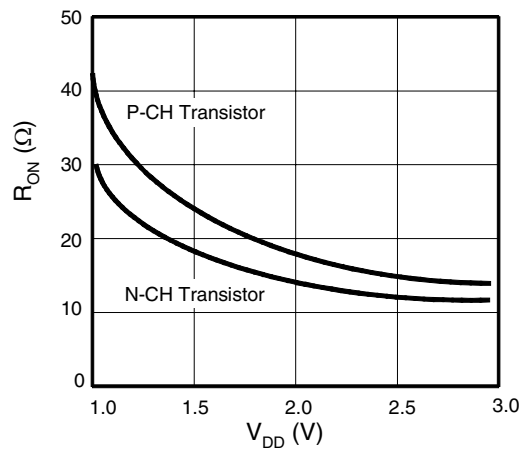**Figure 5.** Typical Output ON-resistance versus Supply Voltage at V_{DS} = 0.2 V
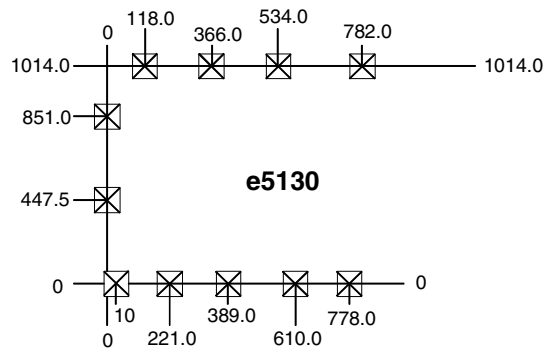

Figure 6. Pad Coordinates

Figure 7. Application Circuit
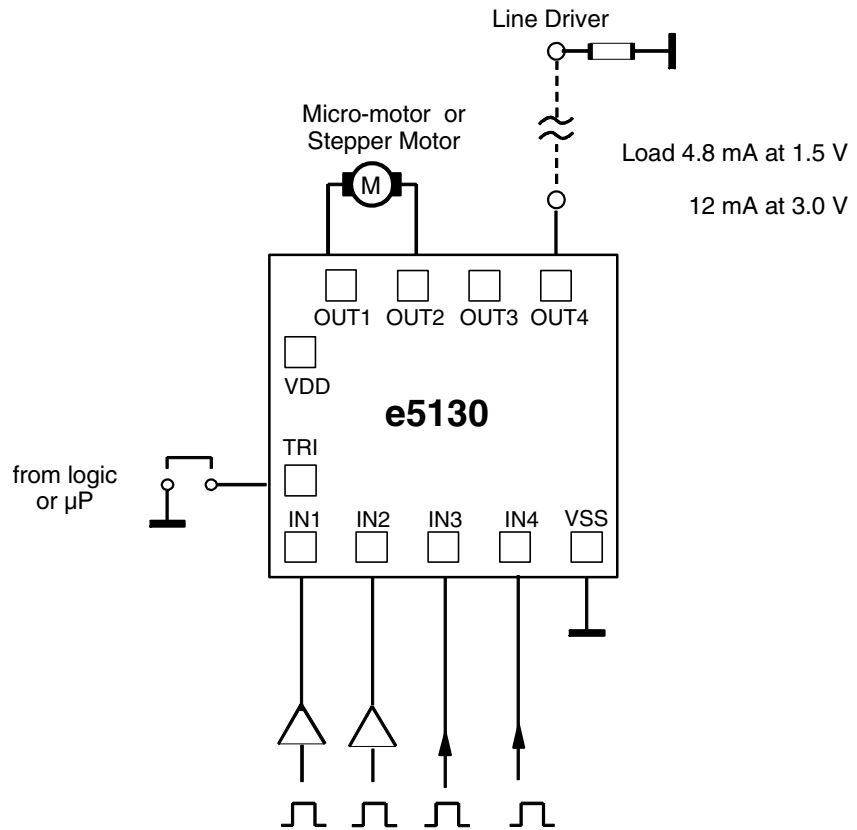
Ordering Information

Extended Type Number	Package	Remarks
e5130-DIT	Die	Die in Trays

![ATMEL logo]

Atmel Corporation

2325 Orchard Parkway
San Jose, CA 95131
Tel: 1(408) 441-0311
Fax: 1(408) 487-2600

Regional Headquarters

Europe

Atmel Sarl
Route des Arsenaux 41
Case Postale 80
CH-1705 Fribourg
Switzerland
Tel: (41) 26-426-5555
Fax: (41) 26-426-5500

Asia

Room 1219
Chinachem Golden Plaza
77 Mody Road Tsimshatsui
East Kowloon
Hong Kong
Tel: (852) 2721-9778
Fax: (852) 2722-1369

Japan

9F, Tonetsu Shinkawa Bldg.
1-24-8 Shinkawa
Chuo-ku, Tokyo 104-0033
Japan
Tel: (81) 3-3523-3551
Fax: (81) 3-3523-7581

Atmel Operations

Memory

2325 Orchard Parkway
San Jose, CA 95131
Tel: 1(408) 441-0311
Fax: 1(408) 436-4314

Microcontrollers

2325 Orchard Parkway
San Jose, CA 95131
Tel: 1(408) 441-0311
Fax: 1(408) 436-4314

La Chantrerie
BP 70602
44306 Nantes Cedex 3, France
Tel: (33) 2-40-18-18-18
Fax: (33) 2-40-18-19-60

ASIC/ASSP/Smart Cards

Zone Industrielle
13106 Rousset Cedex, France
Tel: (33) 4-42-53-60-00
Fax: (33) 4-42-53-60-01

1150 East Cheyenne Mtn. Blvd.
Colorado Springs, CO 80906
Tel: 1(719) 576-3300
Fax: 1(719) 540-1759

Scottish Enterprise Technology Park
Maxwell Building
East Kilbride G75 0QR, Scotland
Tel: (44) 1355-803-000
Fax: (44) 1355-242-743

RF/Automotive

Theresienstrasse 2
Postfach 3535
74025 Heilbronn, Germany
Tel: (49) 71-31-67-0
Fax: (49) 71-31-67-2340

1150 East Cheyenne Mtn. Blvd.
Colorado Springs, CO 80906
Tel: 1(719) 576-3300
Fax: 1(719) 540-1759

Biometrics/Imaging/Hi-Rel MPU/
High Speed Converters/RF Datacom

Avenue de Rochepleine
BP 123
38521 Saint-Egreve Cedex, France
Tel: (33) 4-76-58-30-00
Fax: (33) 4-76-58-34-80

e-mail
literature@atmel.com

Web Site
http://www.atmel.com

Printed on recycled paper.